

	SPEC No. E L O 9 5 1 2 0 ISSUE: Jun. 2, 1997
То;	
S	PECIFICATIONS
Product Type	256k SRAM
	LH52256C-10LL
Model No.	(LH525CL9)
	ifications contains 15 pages including the cover and appendix. we any objections, please contact us before issuing purchasing order.
CUSTOMERS ACCEPTANC	E (5. 16'97.)
DATE:	PRICEPART
BY:	PRESENTED BY: This sent.

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PREPARED BY:

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SHARP CORPORATION



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- When using the products covered herein, please observe the conditions written herein and the precautions outlined in the following paragraphs. In no event shall the company be liable for any damages resulting from failure to strictly adhere to these conditions and precautions.
 - (1) The products covered herein are designed and manufactured for the following application areas. When using the products covered herein for the equipment listed in Paragraph (2), even for the following application areas, be sure to observe the precautions given in Paragraph (2). Never use the products for the equipment listed in Paragraph (3).
 - · Office electronics
 - · Instrumentation and measuring equipment
 - · Machine tools
 - · Audiovisual equipment
 - · Home appliances
 - · Communication equipment other than for trunk lines
 - (2) Those contemplating using the products covered herein for the following equipment which demands high reliability, should first contact a sales representative of the company and then accept responsibility for incorporating into the design fail-sale operation, redundancy, and other appropriate measures for ensuring reliability and safety of the equipment and the overall system.
 - · Control and safety devices for airplanes, trains, automobiles, and other transportation equipment
 - · Mainframe computers
 - · Traffic control systems
 - · Gas leak detectors and automatic cutoff devices
 - · Rescue and security equipment
 - · Other safety devices and safety equipment, etc.
 - (3) Do not use the products covered herein for the following equipment which demands extremely high performance in terms of functionality, reliability, or accuracy.
 - · Aerospace equipment
 - · Communications equipment for trunk lines
 - · Control equipment for the nuclear power industry
 - · Medical equipment related to life support, etc.
 - (4) Please direct all queries and comments regarding the interpretation of the above three Paragraphs to a sales representative of the company.
- Please direct all queries regarding the products covered herein to a sales representative of the company.

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1. Description

The LH52256C-10LL is a static RAM organized as 32, 768 \times 8 bit with provides low-power standby mode.

It is fabricated using silicon-gate CMOS process technology.

Features

OAccess Time	 100 ns (Max.)
Operating current	 4 0 m A (Max.)
	 10 mA (Max. trc. twc=1 μ s)
OStandby current	 4 0 μ A (Max.)
OData retention current	 1.0 μ A (Max. V ccdr = 3 V, Ta = 25 $^{\circ}$ C)
○Wide operating voltage range	 4.5 V to 5.5 V
Operating temperature	 0 ℃ to + 7 0 ℃
OFully static operation	

- OFully static operation
- OThree-state output
- ONot designed or rated as radiation hardened
- \bigcirc 2 8 pin DIP (DIP 2 8 P 6 0 0) plastic package
- ON-type bulk silicon

2. Pin Configuration

			•
A14 🗀	10	28	<u> </u>
A 12 🗀	2	27	□ WE
A 7 🗀	3	26	☐ A 13
A 6	4	25	□ A s
A 5 🗀	5	24	□ A 9
A ₄ □	6	23	<u>A11</u>
Аз 🗆	7	22	□ OE
A 2 🗀	8	21	□ A 10
A 1 =	9	20	CE
A 0	10	19	□ I/O ₈
I/0 ı 🗀	11	18	□ I/O ₇
I/O 2 🗀	12	17	□ I/O 6
I/O3 =	13	16	□ I/O 5
GND ==	14	15	□ I/O ₄
	L		J

Pin Name	Function
A o to A 14	Address inputs
CE	Chip enable
WE	Write enable
ŌE	Output enable
I/O1to I/O8	Data inputs/outputs
Vcc	Power supply
GND	Ground

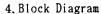
(Top View)

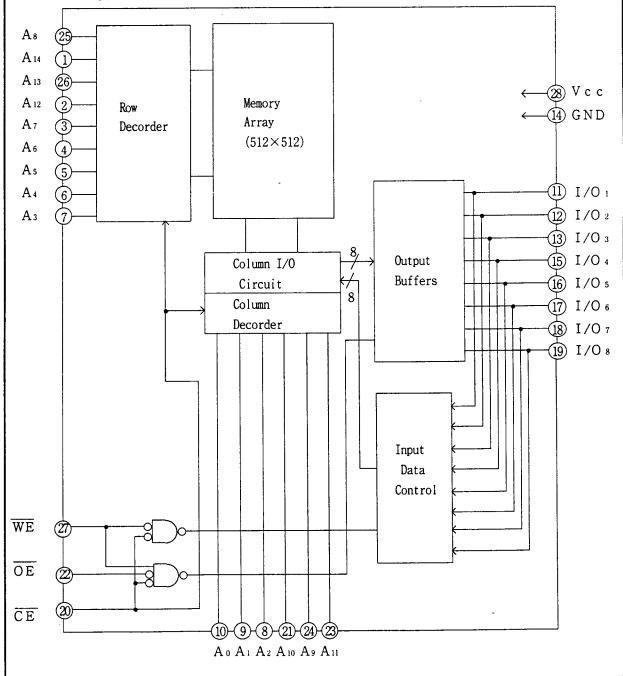
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3. Truth Table

CE	WE	ŌE	Mode	I /O 1 to I /O 8	Supply current
Н	*	*	Standby	High impedance	Standby (Ism)
L	Н	L	Read	Data output	Active (Icc)
L	Н	Н	Output disable	High impedance	Active (Icc)
L	L	*	Write	Data Input	Active (Icc)

(*=Don't Care, L=Low, H=High)





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5. Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Supply voltage (*1)	Vcc	-0.5 to $+7.0$	V
Input voltage(*1)	VIN	-0.5 (*2) to Vcc+0.5	V
Operating temperature	Topr	0 to +70	r
Storage temperature	Tstg	-65 to +150	r

Note) *1. The maximum applicable voltage on any pin with respect to GND.

*2. Undershoot of -3.0V is allowed width of pluse bellow 50ns.

6. Recommended DC Operating Conditions

 $(Ta=0 \ C to + 7 0 \ C)$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	Vcc	4.5	5.0	5.5	V
Input voltage	VIH	2.2		Vcc+0.5	V
	VIL	-0.5 (*3)		0.8	V

Note) *3. Undershoot of -3.0V is allowed width of pluse below 50ns.

7. DC Electrical Characteristics

 $(Ta = 0 \, \text{°C} \text{ to } + 7 \, 0 \, \text{°C}$, $Vcc = 4.5 \, \text{V} \text{ to } 5.5 \, \text{V})$

		(1a - 0 C to 1 7 0 V	,,,,,	Ŧ. U V		
Parameter	Symbol	Conditions	Min.	Typ. (*4)	Max.	Unit
Input leakage	Ili	V _{IN} =OV to Vcc				
current			-1.0		1.0	μΑ
Output leakage	ILO	CE =V _{IH} or OE =V _{IH}				
current		V _{1/0} =0V to Vcc	-1.0	1	1.0	μΑ
Operating	Icc	Minimum cycle				
supply		VIN =VIL or VIH, II/O =OmA, CE =VIL		2 0	4 0	m A
current	Iccı	t_{RC} , $t_{NC} = 1 \mu s$				
		Vin =Vil or Vin, II/0 =OmA, CE =Vil			1 0	m A
Standby	Іѕв	$\overline{CE} \ge V_{cc} - 0.2V$		0.6	4 0	μΑ
current	Isaı	CE =V _{IH}			3_	m A
Output	Vol	IoL= 2.1mA			0.4	V
voltage	Vон	I он= — 1. ОшА	2.4			V

Note) *4. Typical values at Vcc=5.0V, Ta=25 $^{\circ}$ C.



8. AC Electrical Characteristics

AC Test Conditions

Input pulse level	0.6 V to 2.4 V			
Input rise and fall time	1 0 n s			
Input and Output timing Ref. level	1.5 V			
Output load	1TTL+C _L (100pF) (*5)			

Note) *5. Including scope and jig capacitance.

Read cycle

 $(Ta=0 \ C \ to + 7 \ 0 \ C$, $Vcc= 4.5 \ V \ to 5.5$)

Parameter	Symbol	Min.	Max.	Unit
Read cycle time	trc	100		ns
Address access time	t A A		1 0 0	ns
CE access time	t ACE		1 0 0	ns
Output enable to output valid	toe		5 0	ns
Output hold from address change	tон	1 0		ns
CE Low to output active	tız	1 0		ns
OE Low to output active	torz	5		ns
CE High to output in High impedance	tнz	0	4 0	ns
OE High to output in High impedance	tонz	0	4 0	ns

Write cycle

(Ta = 0 % to + 7 0 % , Vcc = 4.5 V to 5.5)

Parameter	Symbol	Min.	Max.	Unit	
Write cycle time	t wc	100		ns	
CE Low to end of write	tcw	8 0		ns	
Address valid to end of write	t aw	8 0		ns	
Address setup time	tas	0		ns	
Write pluse width	twp	7 5		ns	
Write recovery time	twr	0		ns	
Input data setup time	t Dw	4 0		ns	
Input data hold time	t DH	0		ns	
WE High to output active	tow	5		ns	* 6
WE Low to output in High impedance	t wz	0	4 0	ns	* 6
OE High to output in High impedance	tонz	0	4 0	ns	* 6

Note) *6. Active output to High impedance and High impedance to output active tests specified for a $\pm 200 \text{mV}$ transition from steady state levels into the test load.



9. Data Retention Characteristics

(Ta= 0 % to + 7 0 %)

Paramenter	Symbol	Conditions		Min.	Typ. (*7)	Max.	Unit
Data Retention supply voltage	Vccdr	CE≥ Vccdr-0.2V	7	2.0		5.5	V
Data Retention supply current	Iccdr	V CCDR = 3 V	T a = 2 5 °C $T a = 4 0 °C$		0.3	1.0	μ A μ A
Pr		$\overline{CE} \ge V_{CCDR} - 0.2 V$	7			1 5	μΑ
Chip enable setup time	t CDR			0			ns
Chip enable	tr			(*8)			
hold time				trc		· · · · · · · · · · · · · · · · · · ·	ns

Note) ★7. Typical values at Ta=25℃

★8. Read Cycle

10. Pin Capacitance

(Ta=25°C, f=1MHz)

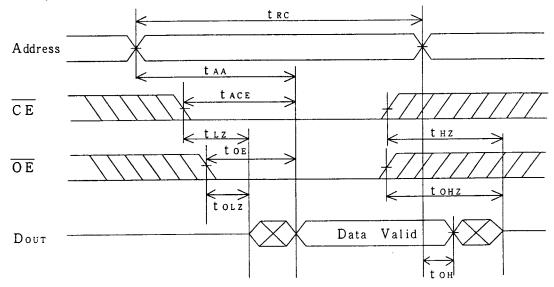
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Input capacitance	CIN	$V_{IN} = 0 V$			7	p F	* 9
I/O capacitance	C1/0	$V_{I/O} = 0 \ V$			1 0	рF	* 9

Note) *9. This parameter is sampled and not production tested.



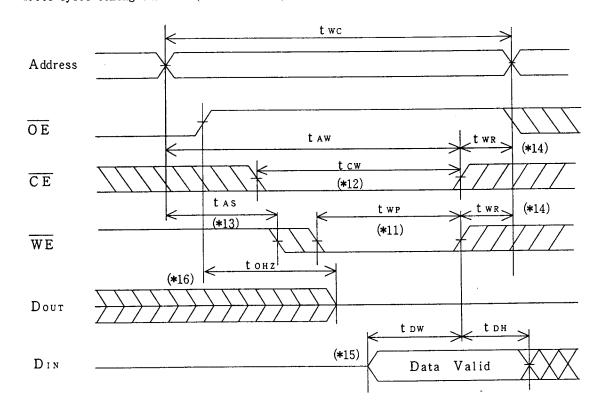
11. Timing Chart

Read cycle timing chart— (*10)



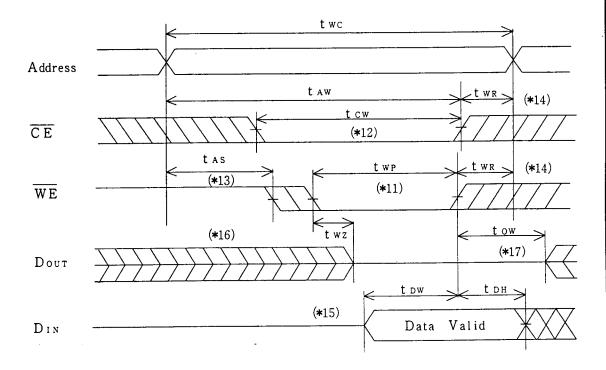
Note) *10. WE is high for Read cycle.

Write cycle timing chart— $\overline{\text{(OE)}}$ Controlled)





Write cycle timing chart— (OE Low fixed)



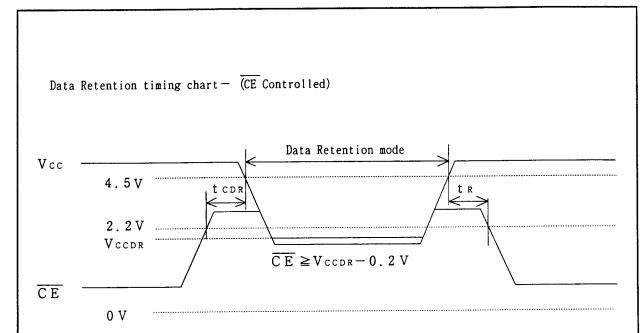
- Note) * 11. A write occurs during the overlap of a low CE, and a low WE,

 A write begins at the latest transition among CE going low, and WE going low.

 A write ends at the earliest transition among CE going high, and WE going high.

 two is measured from the beginning of write to the end of write.
 - * 12. tom is measured from the later of $\overline{\text{CE}}$ going low to the end of write.
 - * 13. tas is measured from the address valid to the beginning of write.
 - * 14. tm is measured from the end of write to the address change.
 - * 15. During this period, I/O pins are in the output state, therefore the input signals of opposite phase to the outputs must not be applied.
 - * 16. If $\overline{\text{CE}}$ goes low simultaneously with $\overline{\text{WE}}$ going low or after $\overline{\text{WE}}$ going low, the outputs remain in high impedance state.
 - * 17. If $\overline{\text{CE}}$ goes high simultaneously with $\overline{\text{WE}}$ going high or before $\overline{\text{WE}}$ going high, the outputs remain in high impedance state.







12 Package and packing specification

 ${\tt 1. \ Package \ Outline \ Specification}$

Refer to drawing No.AA852

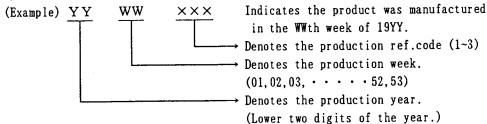
2. Markings

2-1. Marking contents

(1) Product name : LH52256C-10LL

(2) Company name : SHARP

(3) Date code



(4) The marking of "JAPAN" indicates the country of origin.

2-2. Marking layout

Refer to drawing No. AA852

(This layout does not define the dimensions of marking character and marking position.)

3. Packing Specification

3-1. Packing materials

Material Name	Material Specification	Purpose
Magaz ine	Anti-static treated plastic (15devices/magazine)	Packing of device
Stopper	Plastic or rubber	Fixing of device
Label	Paper	Indication of product name, quantity and date of manufacture.
Inner case	Cardboard (600devices/cace)	Fixing of magazine
Outer case	Cardboard	Outer packing of magazine

(Devices shall be inserted into a magazine (sleeve) in the same direction.)

3-2. Outline dimension of magazine (sleeve)

Refer to attached drawing

- 4. Precaution For Unpacking
 - (1) Unpacking should be done on the stand as well as human body treated with anti-ESD.
 - (2) Anti-ESD treatment is given to a magazine.
 Use the equivalent magazine, if it is changed to another one.
 - (3) Be sure to fix two stoppers to both ends of a magazine when storage to prevent the devices from slipping.



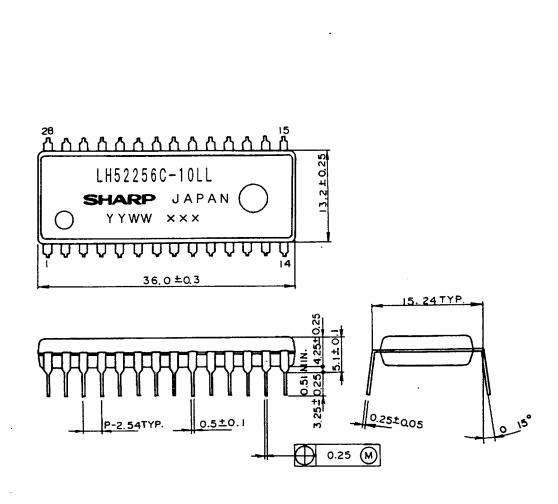
5. Surface Mount Conditions

Please perform the following conditions when mounting ICs not to deteriorate IC quality.

5-1 . Soldering conditions (The following conditions are valid only for one time soldering.)

Mounting Method	Temperature and Duration	Measurement Point
Solder dipping	245℃ or less, duration of less than 3 seconds/dip,	Solder bath.
	total of 5 seconds.	
	(Only the appropriate parts of leads for soldering	
	are immersed in the surface of a jet stream solder	
	bath. During soldering, the solder stream must not	
	come into direct contact with the plastic body of	
	package.)	
Manual soldering	260℃ or less, duration of less than 10 seconds.	IC outer
(soldering iron)	(Only the appropriate parts of leads for soldering	lead surface.
	are soldered with a soldering iron. During soldering,	
	the soldering iron must not come into direct	
	contact with the plastic body of package.)	

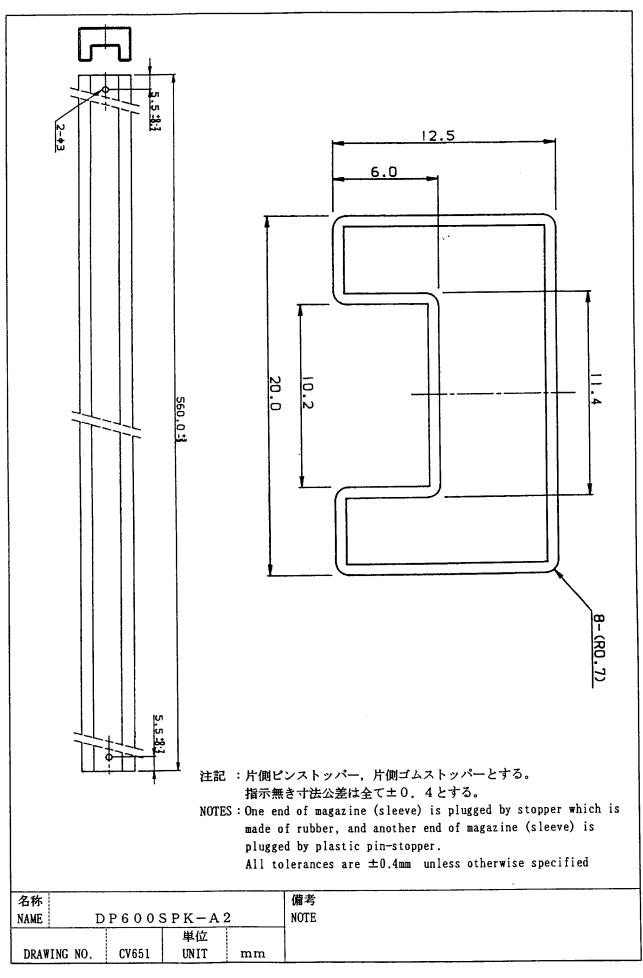




名称]	リード仕上		TIN-LEAD	Γ
NAME	DIP28-P-600		LE	AD FINISH		PLATING	
				単位		<u></u>	
DRAWING NO.		AA85	2	UNIT		mm	

備考 プラスチックパッケージ外が住は、パリを含まないものとする。
NOTE Plastic body dimensions do not include burr of resin.





Static SRAM RAM Random Access Memory LH52256C-10LL 256K (32Kx8) (100 ns) (DIP)